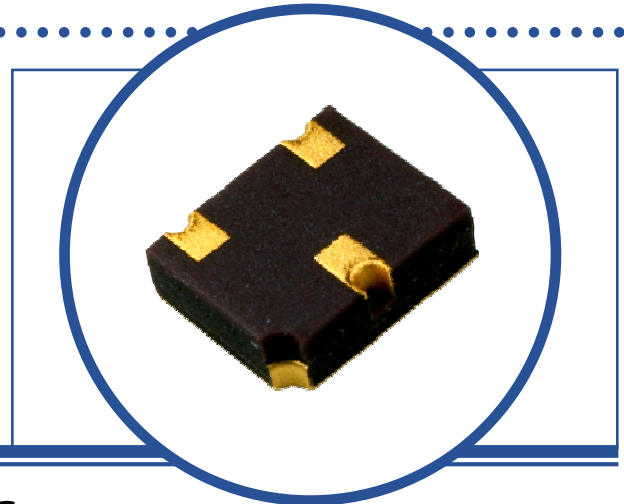


SILICON PLANAR EPITAXIAL PNP TRANSISTOR

2N2906ACSM

- Low Power
- Hermetic Ceramic Surface Mount Package.
- Ideally suited for High Speed Switching and General Purpose Applications
- Screening Options Available



ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise stated)

V _{CBO}	Collector – Base Voltage	-60V
V _{CEO}	Collector – Emitter Voltage	-60V
V _{EBO}	Emitter – Base Voltage	-5V
I _C	Continuous Collector Current	-600mA
P _D	Total Power Dissipation at T _A = 25°C	400mW
	Derate Above 25°C	2.28mW/°C
P _D	Total Power Dissipation at T _C = 25°C	1.8W
	Derate Above 25°C	10.3mW/°C
T _J	Junction Temperature Range	-65 to +200°C
T _{stg}	Storage Temperature Range	-65 to +200°C

THERMAL PROPERTIES

Symbols	Parameters	Min.	Typ.	Max.	Units
R _{θJA}	Thermal Resistance, Junction To Ambient			437.5	°C/W
R _{θJC}	Thermal Resistance, Junction To Case			97.2	°C/W

Semelab Limited reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.



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SILICON PLANAR EPITAXIAL PNP TRANSISTOR 2N2906ACSM

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise stated)

Symbols	Parameters	Test Conditions	Min.	Typ	Max.	Units
$V_{(BR)CEO}^{(1)}$	Collector-Emitter Breakdown Voltage	$I_C = -10\text{mA}$ $I_B = 0$	-60			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = -10\mu\text{A}$ $I_E = 0$	-60			
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = -10\mu\text{A}$ $I_C = 0$	-5			
I_{CEX}	Collector Cut-Off Current	$V_{CE} = -30\text{V}$ $V_{BE} = -0.5\text{V}$			-50	nA
I_{CBO}	Collector Cut-Off Current	$V_{CB} = -50\text{V}$ $I_E = 0$			-0.01	μA
		$T_A = 150^\circ\text{C}$			-10	
$V_{CE(sat)}^{(1)}$	Collector-Emitter Saturation Voltage	$I_C = -150\text{mA}$ $I_B = -15\text{mA}$			-0.4	V
		$I_C = -500\text{mA}$ $I_B = -50\text{mA}$			-1.6	
$V_{BE(sat)}^{(1)}$	Base-Emitter Saturation Voltage	$I_C = -150\text{mA}$ $I_B = -15\text{mA}$			-1.3	
		$I_C = -500\text{mA}$ $I_B = -50\text{mA}$			-2.6	
$h_{FE}^{(1)}$	Forward-current transfer ratio	$I_C = -0.1\text{mA}$ $V_{CE} = -10\text{V}$	40			
		$I_C = -1.0\text{mA}$ $V_{CE} = -10\text{V}$	40			
		$I_C = -10\text{mA}$ $V_{CE} = -10\text{V}$	40			
		$I_C = -150\text{mA}$ $V_{CE} = -10\text{V}$	40		120	
		$I_C = -500\text{mA}$ $V_{CE} = -10\text{V}$	40			

DYNAMIC CHARACTERISTICS

f_T	Transition Frequency	$I_C = -50\text{mA}$ $V_{CE} = -20\text{V}$ $f = 100\text{MHz}$	170			MHz
C_{obo}	Output Capacitance	$V_{CB} = -10\text{V}$ $I_E = 0$ $f = 1.0\text{MHz}$			8	pF
C_{ibo}	Input Capacitance	$V_{EB} = -2\text{V}$ $I_C = 0$ $f = 1.0\text{MHz}$			30	
t_{on}	Turn-On Time	$I_C = -150\text{mA}$ $V_{CC} = -30\text{V}$ $I_{B1} = -15\text{mA}$			45	ns
t_{off}	Turn-Off Time	$I_C = -150\text{mA}$ $V_{CC} = -30\text{V}$ $I_{B1} = -I_{B2} = -15\text{mA}$			300	

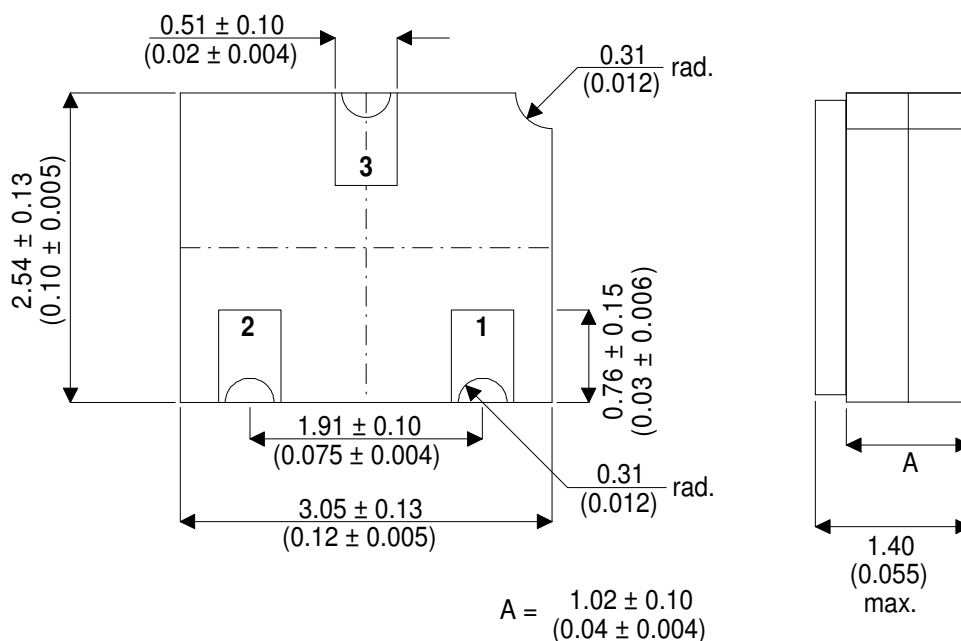
Notes

(1) Pulse Width $\leq 300\mu\text{s}$, $\delta \leq 2\%$

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MECHANICAL DATA

Dimensions in mm (inches)



LCC1

Underside View

Pad 1 - Base

Pad 2 - Emitter

Pad 3 - Collector